





### **SOT-23 Formed SMD Package**

BC817 BC818

## SILICON PLANAR EPITAXIAL TRANSISTORS

N-P-N transistors

#### Marking

BC817 = 6D

BC817-16 = 6A

BC817-25 = 6B

BC817-40 = 6C

BC818 = 6H

BC818-16 = 6E

BC818-25 = 6F

BC818-40 = 6G

## Pin configuration

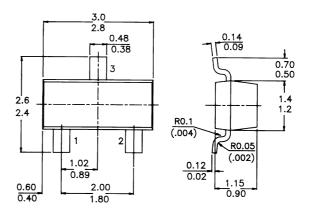
1 = BASE

2 = EMITTER

3 = COLLECTOR



# PACKAGE OUTLINE DETAILS ALL DIMENSIONS IN mm



### ABSOLUTE MAXIMUM RATINGS

		BC817		BC81	BC818	
Collector–emitter voltage $(V_{BE} = 0)$	$V_{CES}$	max.	50	30	$\overline{V}$	
Collector-emitter voltage (open base)	$V_{CE0}$	max.	45	25	V	
Collector current (peak value)	$I_{CM}$	max.	1	000	mA	
Total power dissipation up to $T_{amb} = 25$ °C	$P_{tot}$	max.	2	250	mW	
Junction temperature	$T_j$	max.	1	50	$^{\circ}$ C	
Transition frequency at $f = 100 \text{ MHz}$	,					
$I_C = 10mA; V_{CE} = 5V$	$f_T$	>	1	.00	MHz	

<b>RATINGS</b> (at $T_A = 25^{\circ}$ C unit	less otherwise spec	ified)					
Limiting values	,	•		BC817 BC83		BC81	8
Collector–emitter voltage (V <sub>BE</sub>	= 0	$V_{CES}$	max.	50		30	$\overline{V}$
Collector-emitter voltage (ope	n base)						
$I_C = 10 \ mA$		$V_{CE0}$	max.	45		25	V
Emitter-base voltage (open co	ollector)	$V_{EB0}$	max.	5		5	V
Collector current (d.c.)		$I_C$	max.		500		mA
Collector current (peak value)		$I_{CM}$	max.	1000			mA
Emitter current (peak value)		$-I_{EM}$	max.	1000			mA
Base current (d.c.)		$I_B$	max.		100		
Base current (peak value)		$I_{BM}$	max.	200			mA
Total power dissipation up to	$T_{amb} = 25  ^{\circ}C$	$P_{tot}$	max.	250			mW
Storage temperature		$T_{stg}$		−55 to +150			° C
Junction temperature		$T_j$	max.	150			° C
,		,					
THERMAL RESISTANCE							
From junction to ambient				F	Rth j–a =	500	KW
CHARACTERISTICS							
$T_i = 25$ °C unless otherwise s	enecified						
Collector cut-off current	ресуши						
$I_E = 0$ ; $V_{CB} = 20 \text{ V}$ ; $T_i =$	25. ℃			Lane		100	11 A
				$I_{CB0}$	<		
$I_E = 0$ ; $V_{CB} = 20V$ ; $T_j = 1$ Emitter cut-off current	150 C			$I_{CB0}$	<	3	$\mu A$
				I	,	10	1
$I_C = 0$ ; $V_{EB} = 5 V$				$I_{EB0}$	<	10	$\mu A$
Base emitter voltage *				17		1 2	1.7
$l_C = 500 \text{ mA}; V_{CE} = 1 \text{ V}$				$V_{BE}$	<	1,2	V
Saturation voltage				17		700	17
$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$				$V_{CEsat}$	<	700	mV
D.C. current gain				1		10	
$I_C = 500 \text{ mA}; V_{CE} = 1 \text{ V}$	DC017/DC010			$h_{FE}$	>	40	
$I_C = 100 \ mA; \ V_{CE} = 1 \ V_{CE}$	; BC81// BC818			$h_{FE}$	100 to	600	
	BC817-16			4	100 to	250	
	BC818-16			$h_{FE}$	100 to	230	
	BC817-25						
				$h_{FE}$	160 to	400	
	BC818-25						
	BC817-40			1	250 (-	<i>c</i> 00	
	BC818-40			$h_{FE}$	250 to	600	
Transition frequency at $f = 10$	0 MHz						
$I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$	-			$f_T$	>	100	MHz.
Collector capacitance at $f = 1$	MHz			, 1	-	_00	
$I_E = I_e = 0; V_{CB} = 10V$	<del></del>			$C_c$	typ.	5	рF
$I_{E} = I_{e} = 0$ , $I_{CB} = 10$				$\sim_{\mathcal{C}}$	197.	J	P -

### **Notes**

# **Disclaimer**

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